



HBR2150

主要参数 MAIN CHARACTERISTICS

$I_{F(AV)}$	2A
V_{RRM}	150 V
T_j	175 °C
$V_{F(max)}$	0.76V (@ $T_j=125^{\circ}C$)

用途

- 低压、高频整流
- 低压续流电路和保护电路

APPLICATIONS

- Low voltage, high frequency rectifier
- Free wheeling diodes, polarity protection applications

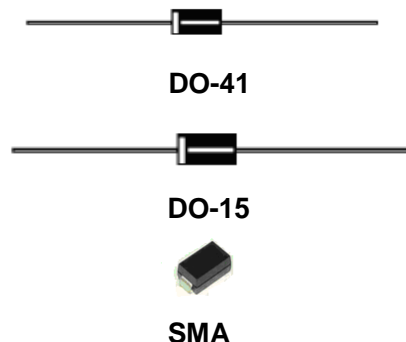
产品特性

- 轴向结构
- 低功耗，高效率
- 良好的高温特性
- 有过压保护环，高可靠性
- 环保（RoHS）产品

FEATURES

- Axial Lead Rectifier
- Low power loss, high efficiency
- High Operating Junction Temperature
- Guard ring for overvoltage protection, High reliability
- RoHS product

封装 Package



订货信息 ORDER MESSAGE

订货型号 Order codes				印 记 Marking	封 装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen Free-Tube	有卤-编带 Halogen-Reel	无卤-编带 Halogen Free-Reel		
N/A	N/A	HBR2150-DC-A	HBR2150-DC-AR	HBR2150	DO-41
N/A	N/A	HBR2150-DB-A	HBR2150-DB-AR	HBR2150	DO-15
N/A	N/A	HBR2150-XA-A	HBR2150-XA-AR	HBR2150	SMA



**绝对最大额定值 ABSOLUTE RATINGS (Tc=25℃)**

项 目 Parameter	符 号 Symbol	数 值 Value	单 位 Unit
最大反向重复峰值电压 Repetitive peak reverse voltage	V_{RRM}	150	V
最大直流阻断电压 Maximum DC blocking voltage	V_{DC}	150	V
正向平均整流电流T _c =125℃ Average Rectified Forward Current	$I_{F(AV)}$	2	A
正向峰值浪涌电流 Surge non repetitive forward current (额定负载 8.3ms 半正弦波—按 JEDEC 方法) 8.3 ms single half-sine-wave (JEDEC Method)	I_{FSM}	50	A
最高结温 Maximum junction temperature	T_j	175	℃
储存温度 Storage temperature range	T_{STG}	-40~+150	℃

电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	测试条件 Tests conditions		最小值 Value(min)	典型值 Value(typ)	最大值 Value(max)	单 位 Unit
I_R	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			10	μA
	$T_j = 125^\circ\text{C}$				5	mA
V_F	$T_j = 25^\circ\text{C}$	$I_F = 2\text{A}$		0.80	0.9	V
	$T_j = 125^\circ\text{C}$			0.70	0.76	V

热特性 THERMAL CHARACTERISTICS

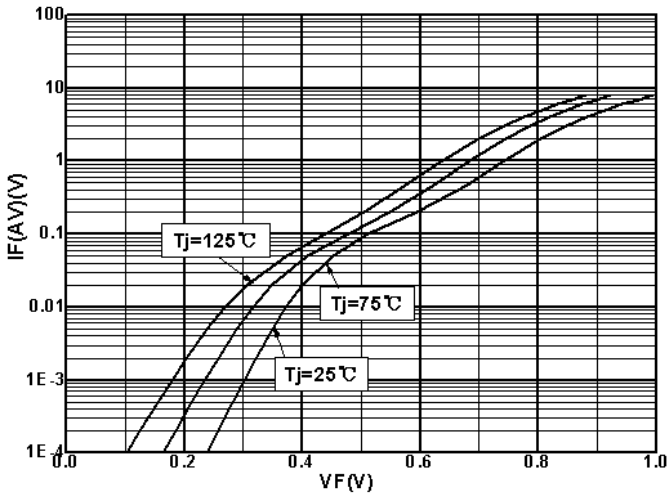
项 目 Parameter		符 号 Symbol	最小值 Value(min)	最大值 Value(max)	单 位 Unit
结到环境的热阻 Thermal resistance from junction to ambient	DO-41	$R_{th(j-a)}$		100	℃/W
	DO-15			85	
	SMA			150	
结到管壳的热阻 Thermal resistance from junction to case	DO-41	$R_{th(j-c)}$		50	℃/W
	DO-15			40	
	SMA			50	



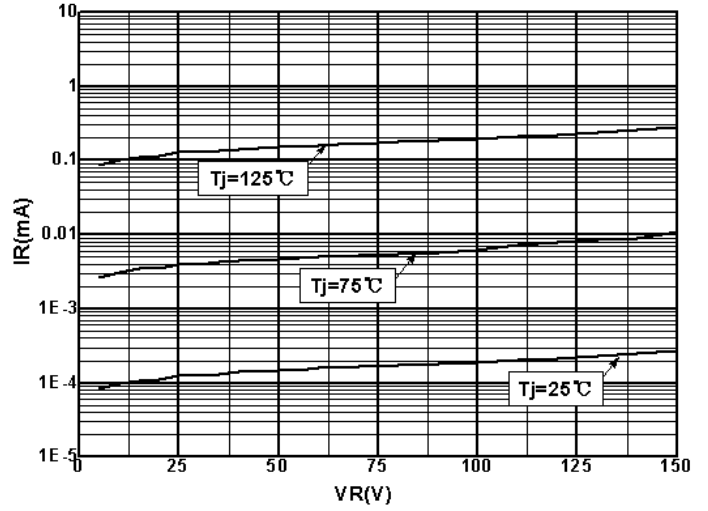


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

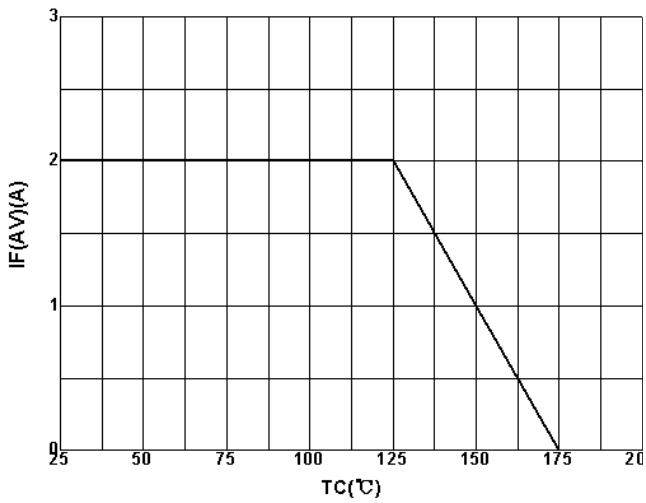
IF vs VF



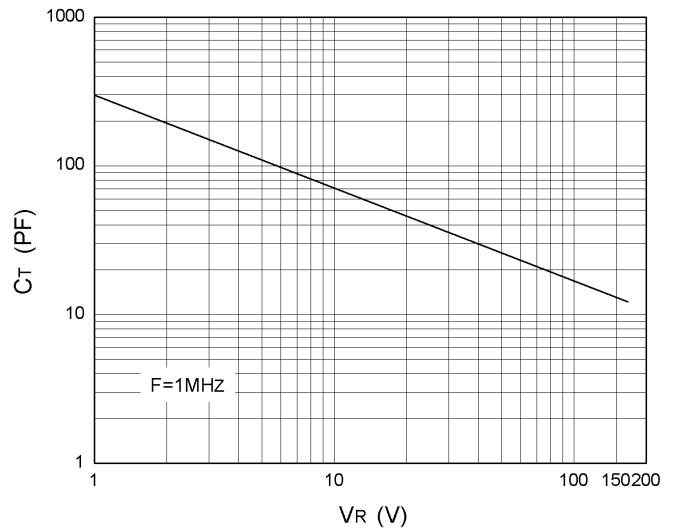
IR vs VR

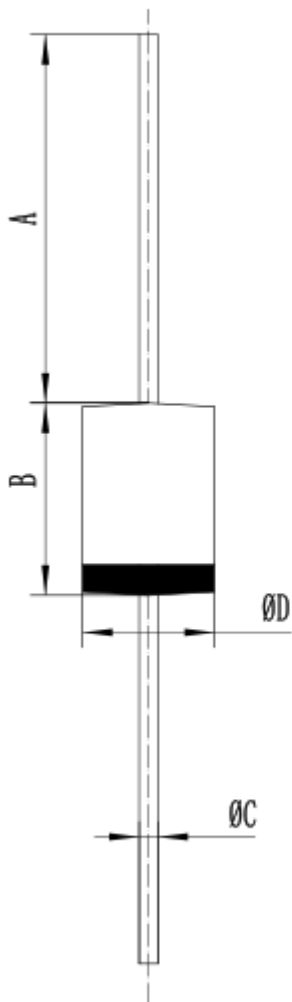


IF(AV) vs TC



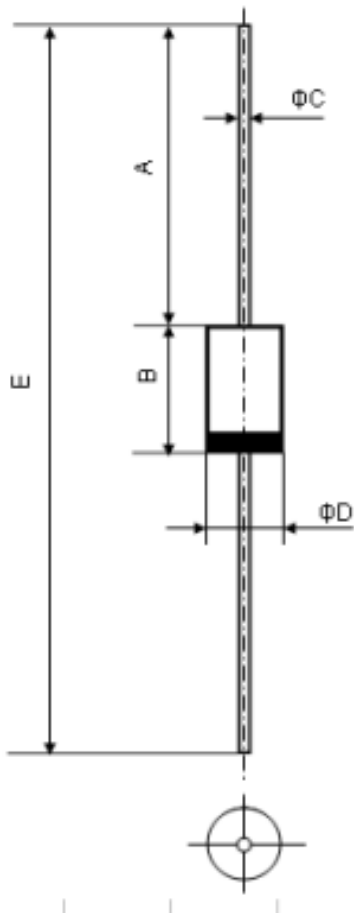
CJ vs VR





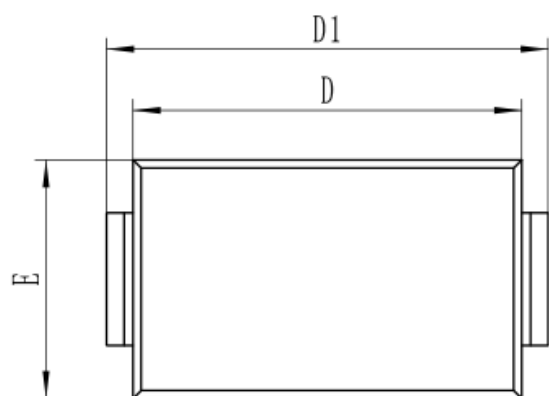
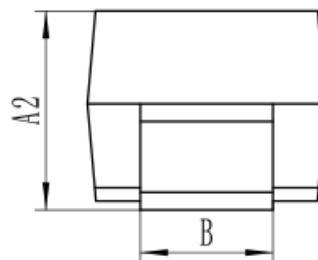
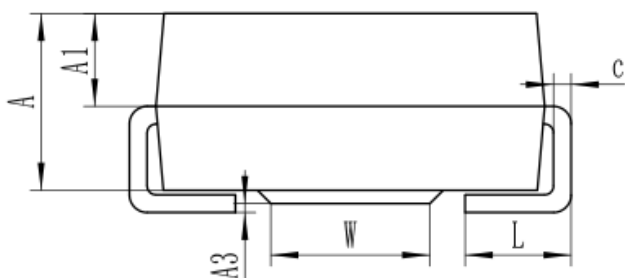
符号 symbol	Min	Max
A	25.4	-
B	4.2	5.2
C	0.6	0.9
D	2	3





符号 symbol	Min	Max
A	25.4	—
B	5.8	7.6
C	0.7	0.9
D	2.6	3.6





SYMBOL	MM	
	MIN	MAX
A	1.60	2.40
A1	0.85	1.25
A2	1.90	2.65
A3	0.10	0.25
B	1.30	1.70
c	0.15	0.31
D	4.00	4.70
D1	4.70	5.30
E	2.40	2.90
L	0.76	1.55
W	1.50	2.10





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